

MRF6S9045NR1 replaced by MRFE6S9045NR1. Refer to Device Migration PCN12895 for more details. MRF6S9045NBR1 no longer manufactured.

RF Power Field Effect Transistors

N-Channel Enhancement-Mode Lateral MOSFETs

Designed for broadband commercial and industrial applications with frequencies up to 1000 MHz. The high gain and broadband performance of these devices make them ideal for large-signal, common-source amplifier applications in 28 volt base station equipment.

- Typical Single-Carrier N-CDMA Performance @ 880 MHz, $V_{DD} = 28$ Volts, $I_{DQ} = 350$ mA, $P_{out} = 10$ Watts Avg., IS-95 CDMA (Pilot, Sync, Paging, Traffic Codes 8 Through 13) Channel Bandwidth = 1.2288 MHz. PAR = 9.8 dB @ 0.01% Probability on CCDF.
 - Power Gain — 22.7 dB
 - Drain Efficiency — 32%
 - ACPR @ 750 kHz Offset — -47 dBc in 30 kHz Bandwidth

GSM EDGE Application

- Typical GSM EDGE Performance: $V_{DD} = 28$ Volts, $I_{DQ} = 350$ mA, $P_{out} = 16$ Watts Avg., Full Frequency Band (921-960 MHz)
 - Power Gain — 20 dB
 - Drain Efficiency — 46%
 - Spectral Regrowth @ 400 kHz Offset = -62 dBc
 - Spectral Regrowth @ 600 kHz Offset = -78 dBc
 - EVM — 1.5% rms

GSM Application

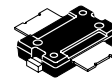
- Typical GSM Performance: $V_{DD} = 28$ Volts, $I_{DQ} = 350$ mA, $P_{out} = 45$ Watts, Full Frequency Band (921-960 MHz)
 - Power Gain — 20 dB
 - Drain Efficiency — 68%
- Capable of Handling 5:1 VSWR, @ 28 Vdc, 880 MHz, 45 Watts CW Output Power

Features

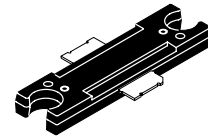
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Integrated ESD Protection
- 225°C Capable Plastic Package
- N Suffix Indicates Lead-Free Terminations. RoHS Compliant.
- TO-270-2 in Tape and Reel. R1 Suffix = 500 Units per 24 mm, 13 inch Reel.
- TO-272-2 in Tape and Reel. R1 Suffix = 500 Units per 44 mm, 13 inch Reel.

MRF6S9045NR1
MRF6S9045NBR1

880 MHz, 10 W AVG., 28 V
SINGLE N-CDMA
LATERAL N-CHANNEL
BROADBAND RF POWER MOSFETs



CASE 1265-09, STYLE 1
TO-270-2
PLASTIC
MRF6S9045NR1



CASE 1337-04, STYLE 1
TO-272-2
PLASTIC
MRF6S9045NBR1

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	- 0.5, +68	Vdc
Gate-Source Voltage	V_{GS}	- 0.5, +12	Vdc
Storage Temperature Range	T_{stg}	- 65 to +150	°C
Case Operating Temperature	T_C	150	°C
Operating Junction Temperature (1,2)	T_J	225	°C

1. Continuous use at maximum temperature will affect MTTF.

2. MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (1,2)	Unit
Thermal Resistance, Junction to Case Case Temperature 81°C, 45 W CW Case Temperature 79°C, 10 W CW	$R_{\theta JC}$	1.0 1.1	°C/W

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	1A (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	IV (Minimum)

Table 4. Moisture Sensitivity Level

Test Methodology	Rating	Package Peak Temperature	Unit
Per JESD 22-A113, IPC/JEDEC J-STD-020	3	260	°C

Table 5. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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Off Characteristics

Zero Gate Voltage Drain Leakage Current ($V_{DS} = 68\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	1	μAdc
Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc

On Characteristics

Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 200\text{ }\mu\text{A}$)	$V_{GS(th)}$	1	2	3	Vdc
Gate Quiescent Voltage ($V_{DD} = 28\text{ Vdc}$, $I_D = 350\text{ mAdc}$, Measured in Functional Test)	$V_{GS(Q)}$	2	2.9	4	Vdc
Drain-Source On-Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 1.0\text{ Adc}$)	$V_{DS(on)}$	—	0.22	0.3	Vdc

Dynamic Characteristics

Input Capacitance ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz)	C_{iss}	—	77	—	pF
Output Capacitance ($V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{oss}	—	27	—	pF
Reverse Transfer Capacitance ($V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{rss}	—	0.78	—	pF

Functional Tests (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 350\text{ mA}$, $P_{out} = 10\text{ W Avg.}$, $f = 880\text{ MHz}$, Single-Carrier N-CDMA, 1.2288 MHz Channel Bandwidth Carrier. ACPR measured in 30 kHz Channel Bandwidth @ $\pm 750\text{ kHz}$ Offset. PAR = 9.8 dB @ 0.01% Probability on CCDF

Power Gain	G_{ps}	21	22.7	25	dB
Drain Efficiency	η_D	30.5	32	—	%
Adjacent Channel Power Ratio	ACPR	—	-47	-45	dBc
Input Return Loss	IRL	—	-20 -20	-9 -7	dB

1. MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.
2. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

(continued)

Table 5. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted) **(continued)**

Characteristic	Symbol	Min	Typ	Max	Unit
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Typical GSM EDGE Performances (In Freescale GSM EDGE Test Fixture Optimized for 921 - 960 MHz, 50 ohm system)

$V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 350\text{ mA}$, $P_{out} = 16\text{ W Avg.}$, $f = 921\text{ - }960\text{ MHz}$, GSM EDGE Signal

Power Gain	G_{ps}	—	20	—	dB
Drain Efficiency	η_D	—	46	—	%
Error Vector Magnitude	EVM	—	1.5	—	%
Spectral Regrowth at 400 kHz Offset	SR1	—	-62	—	dBc
Spectral Regrowth at 600 kHz Offset	SR2	—	-78	—	dBc

Typical CW Performances (In Freescale GSM Test Fixture Optimized for 921 - 960 MHz, 50 ohm system) $V_{DD} = 28\text{ Vdc}$,

$I_{DQ} = 350\text{ mA}$, $P_{out} = 45\text{ W}$, $f = 921\text{ - }960\text{ MHz}$

Power Gain	G_{ps}	—	20	—	dB
Drain Efficiency	η_D	—	68	—	%
Input Return Loss	IRL	—	-12	—	dB
P_{out} @ 1 dB Compression Point ($f = 940\text{ MHz}$)	P1dB	—	52	—	W

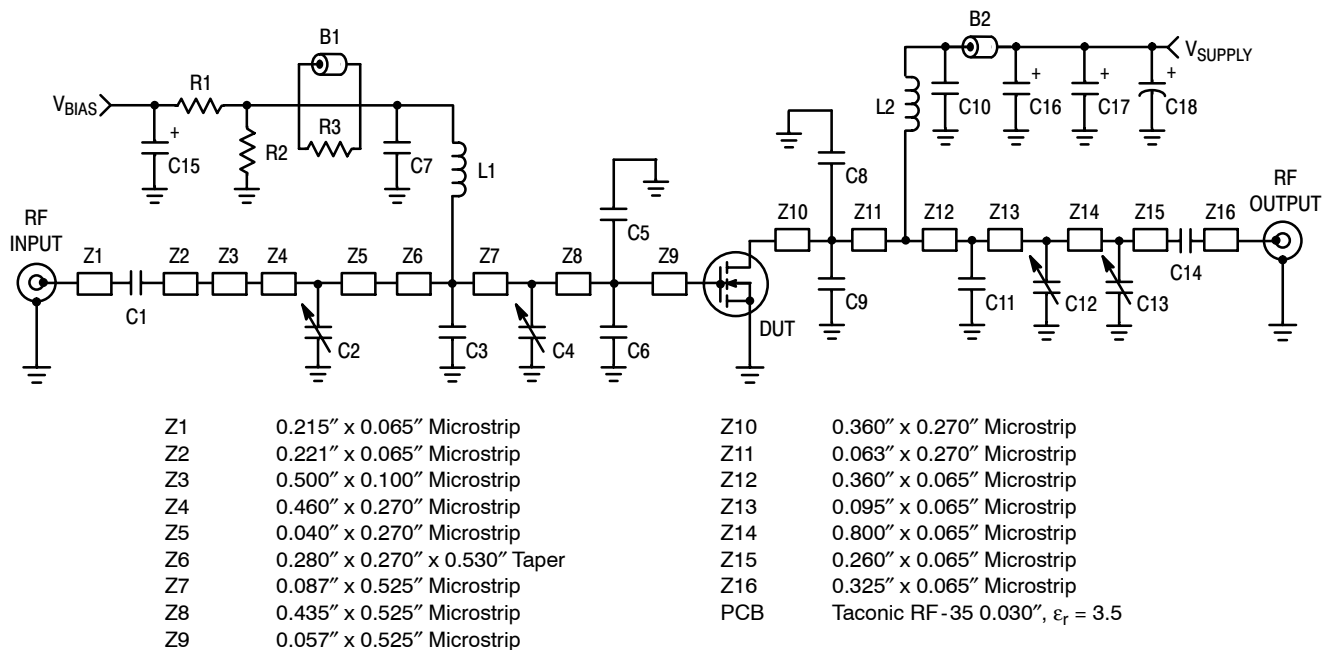


Figure 1. MRF6S9045NR1(NBR1) Test Circuit Schematic

Table 6. MRF6S9045NR1(NBR1) Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
B1	Ferrite Bead	2743019447	Fair Rite
B2	Ferrite Bead	2743021447	Fair Rite
C1, C7, C10, C14	47 pF Chip Capacitors	ATC100B470JT500XT	ATC
C2, C4, C12	0.8-8.0 pF Variable Capacitors, Gigatrim	27291SL	Johanson
C3	15 pF Chip Capacitor	ATC100B150JT500XT	ATC
C5, C6	12 pF Chip Capacitors	ATC100B120JT500XT	ATC
C8, C9	13 pF Chip Capacitors	ATC100B130JT500XT	ATC
C11	7.5 pF Chip Capacitor	ATC100B7R5JT500XT	ATC
C13	0.6-4.5 pF Variable Capacitor, Gigatrim	27271SL	Johanson
C15, C16, C17	10 μ F, 35 V Tantalum Capacitors	T491D106K035AT	Kemet
C18	220 μ F, 50 V Electrolytic Capacitor	EMVY500ADA221MJA0G	Nippon Chemi-Con
L1, L2	12.5 nH Inductor	A04T-5	Coilcraft
R1	1 k Ω , 1/4 W Chip Resistor	CRCW12061001FKEA	Vishay
R2	560 k Ω , 1/4 W Chip Resistor	CRCW12065600FKEA	Vishay
R3	12 Ω , 1/4 W Chip Resistor	CRCW120612R0FKEA	Vishay

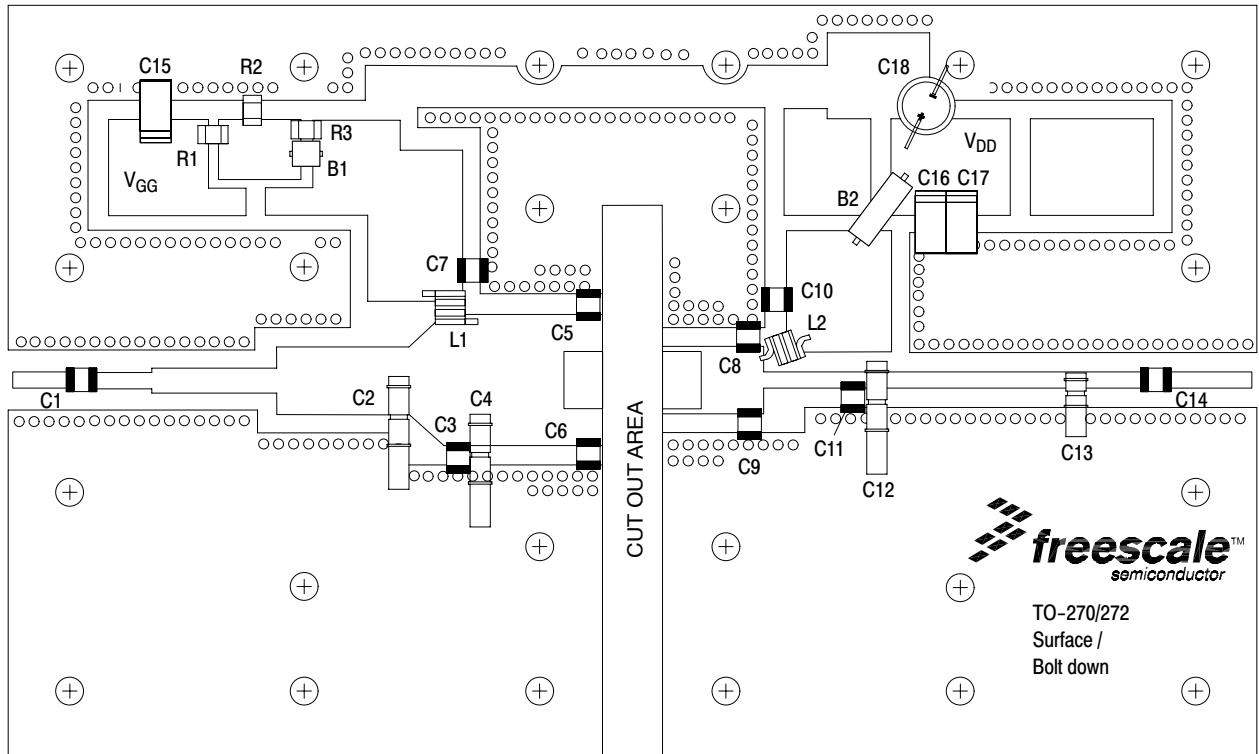


Figure 2. MRF6S9045NR1 (NBR1) Test Circuit Component Layout

TYPICAL CHARACTERISTICS

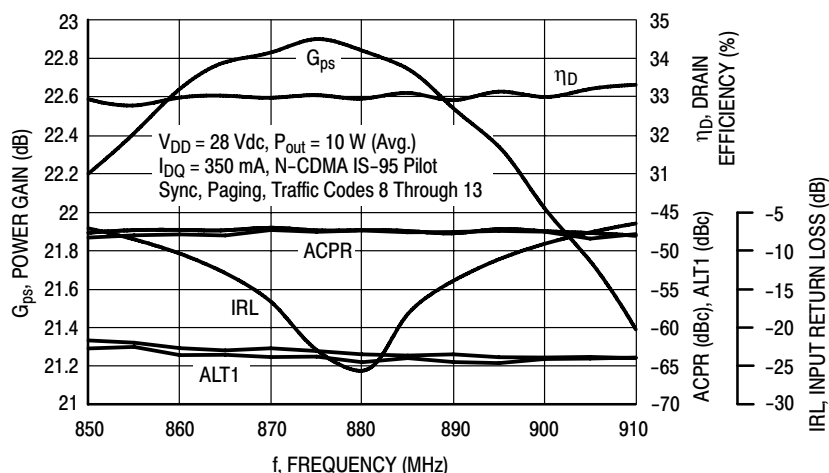


Figure 3. Single-Carrier N-CDMA Broadband Performance @ $P_{out} = 10$ Watts Avg.

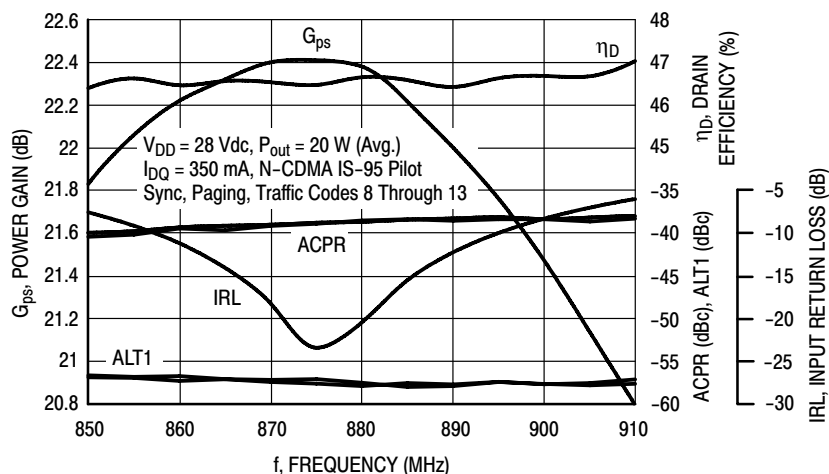


Figure 4. Single-Carrier N-CDMA Broadband Performance @ $P_{out} = 20$ Watts Avg.

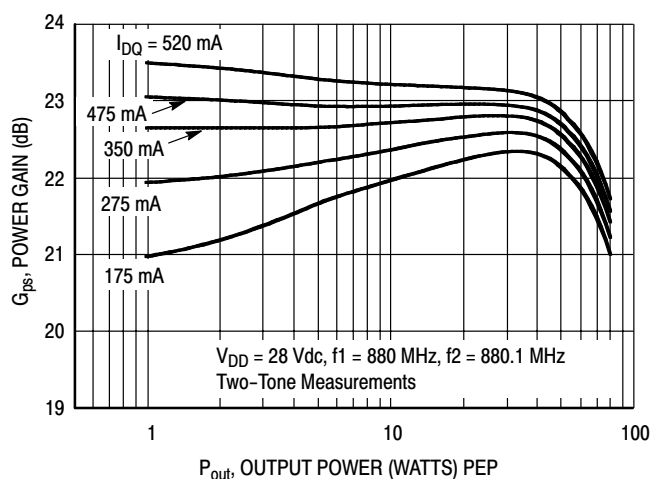


Figure 5. Two-Tone Power Gain versus Output Power

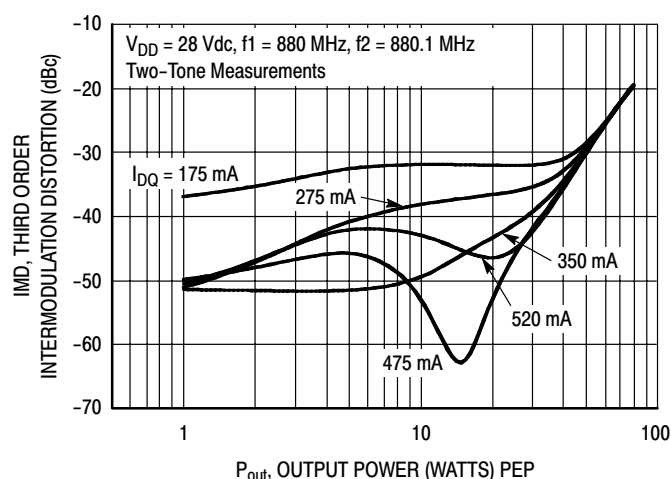


Figure 6. Third Order Intermodulation Distortion versus Output Power

TYPICAL CHARACTERISTICS

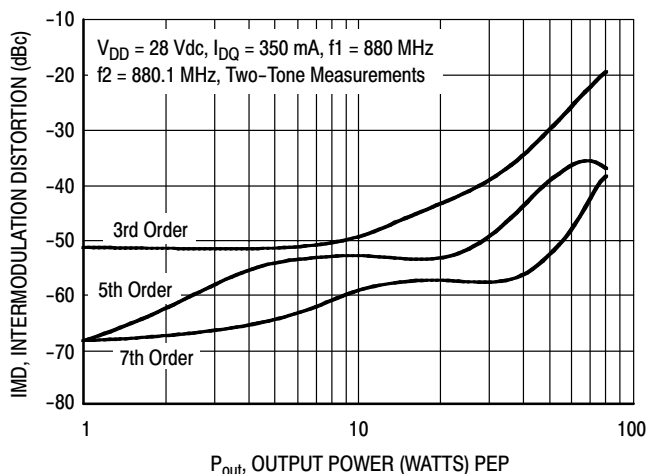


Figure 7. Intermodulation Distortion Products versus Output Power

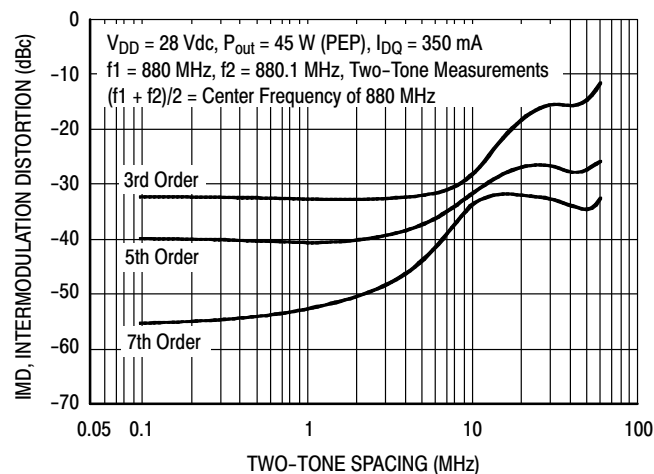


Figure 8. Intermodulation Distortion Products versus Tone Spacing

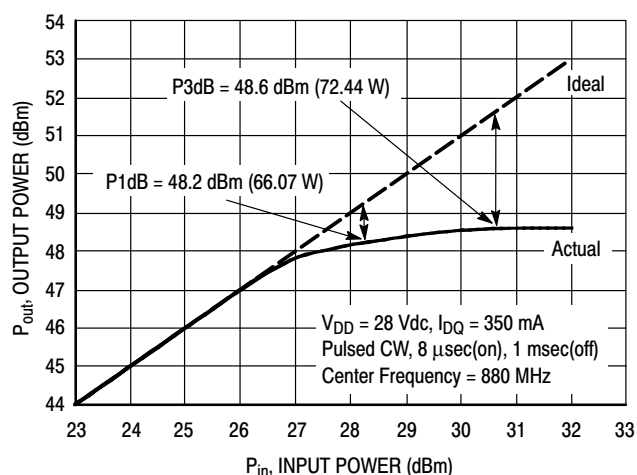


Figure 9. Pulsed CW Output Power versus Input Power

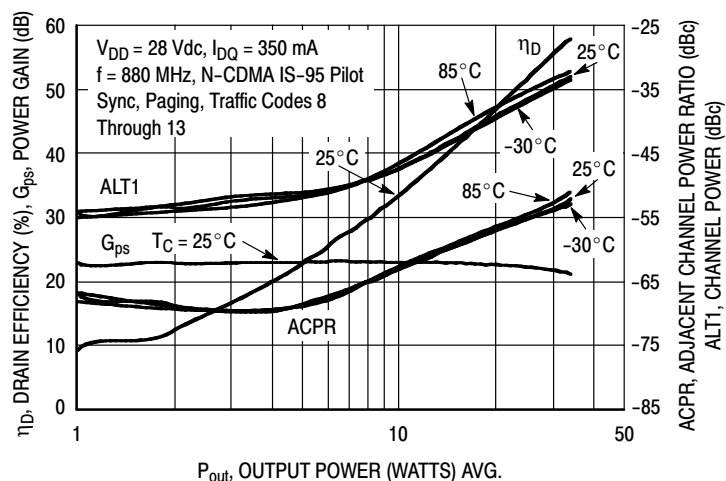


Figure 10. Single-Carrier N-CDMA ACPR, ALT1, Power Gain and Drain Efficiency versus Output Power

TYPICAL CHARACTERISTICS

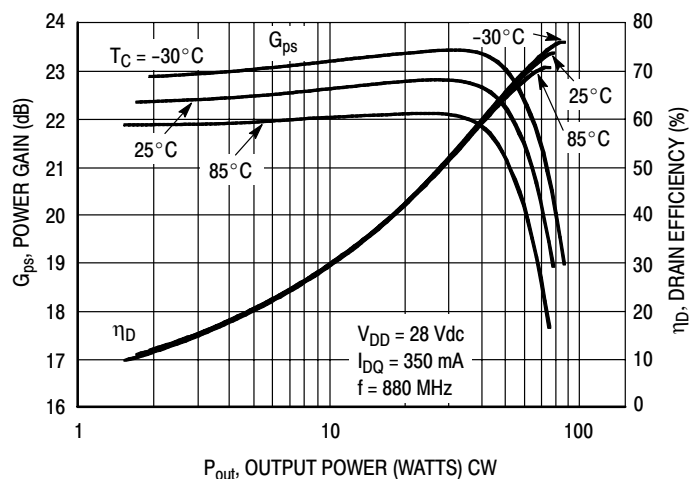


Figure 11. Power Gain and Drain Efficiency versus CW Output Power

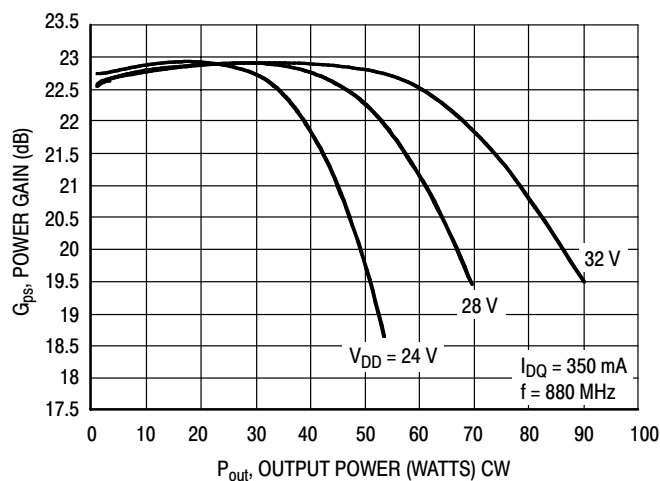
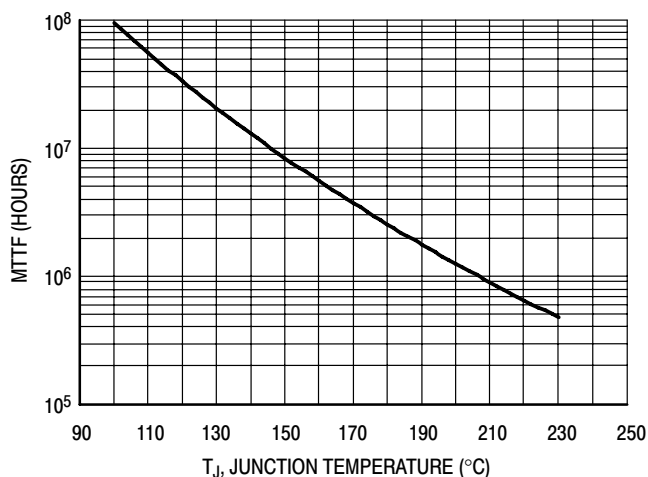


Figure 12. Power Gain versus Output Power



This above graph displays calculated MTTF in hours when the device is operated at $V_{DD} = 28\text{ Vdc}$, $P_{out} = 10\text{ W Avg.}$, and $\eta_D = 32\%$.

MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.

Figure 13. MTTF Factor versus Junction Temperature

N-CDMA TEST SIGNAL

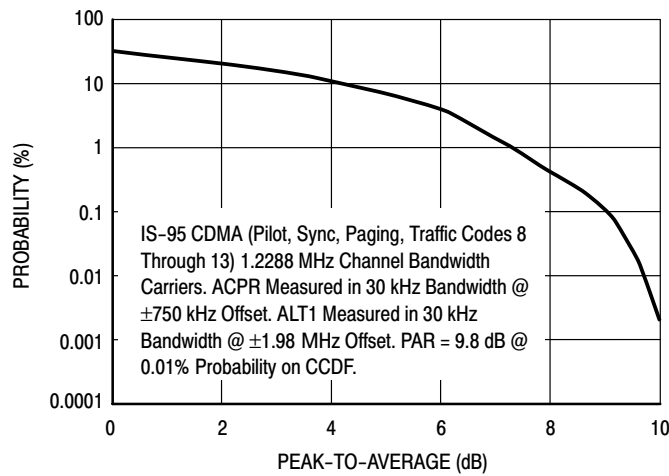


Figure 14. Single-Carrier CCDF N-CDMA

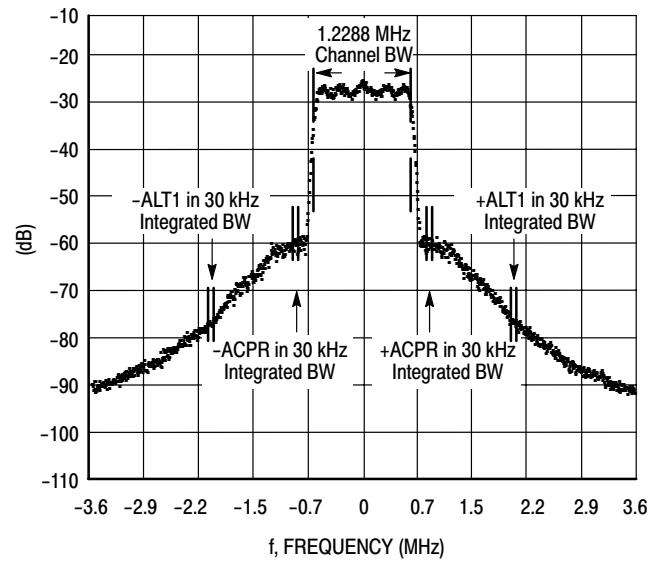
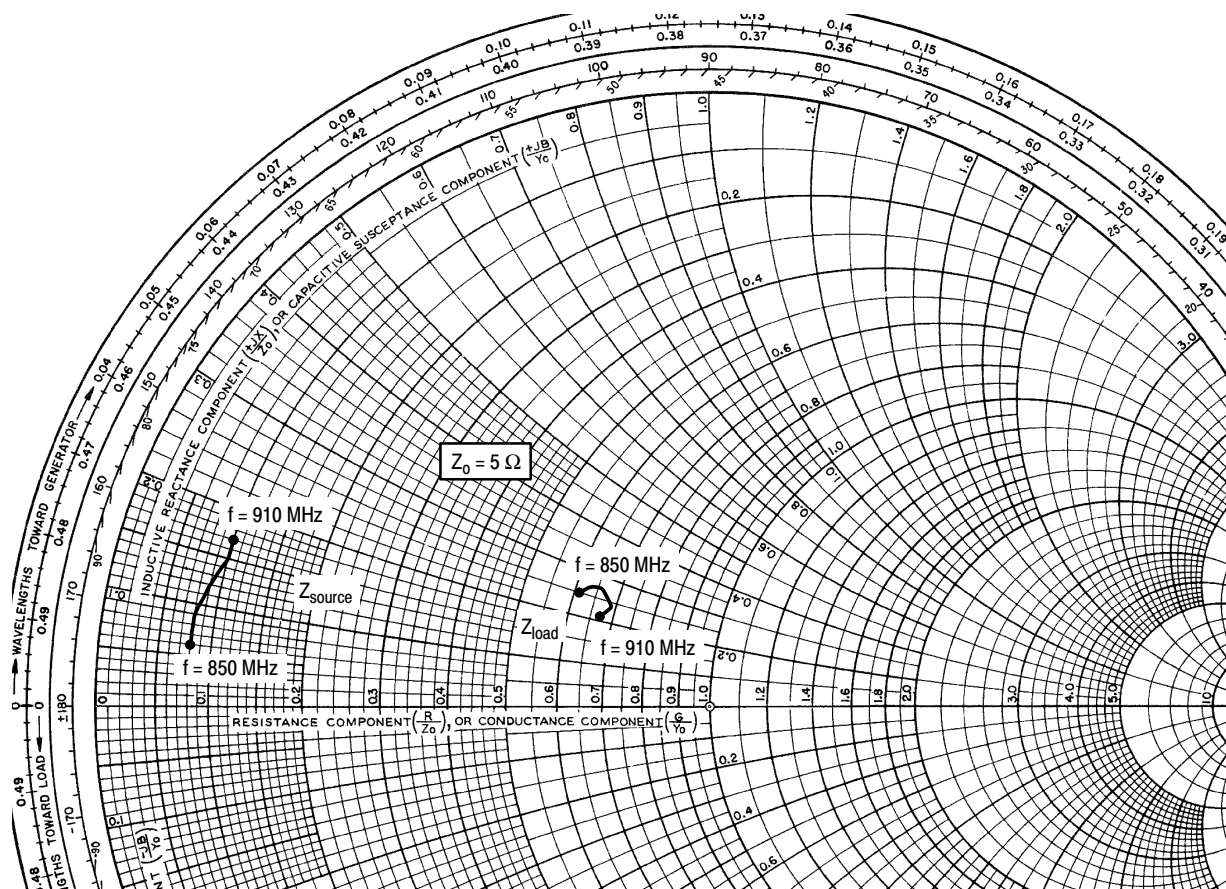


Figure 15. Single-Carrier N-CDMA Spectrum



$V_{DD} = 28 \text{ Vdc}$, $I_{DQ} = 350 \text{ mA}$, $P_{out} = 10 \text{ W Avg.}$

f MHz	Z_{source} Ω	Z_{load} Ω
850	$0.42 + j0.30$	$3.05 + j1.27$
865	$0.42 + j0.44$	$3.16 + j1.33$
880	$0.45 + j0.60$	$3.31 + j1.33$
895	$0.48 + j0.74$	$3.43 + j1.20$
910	$0.50 + j0.85$	$3.35 + j1.05$

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

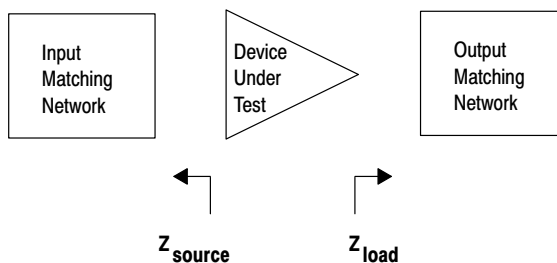
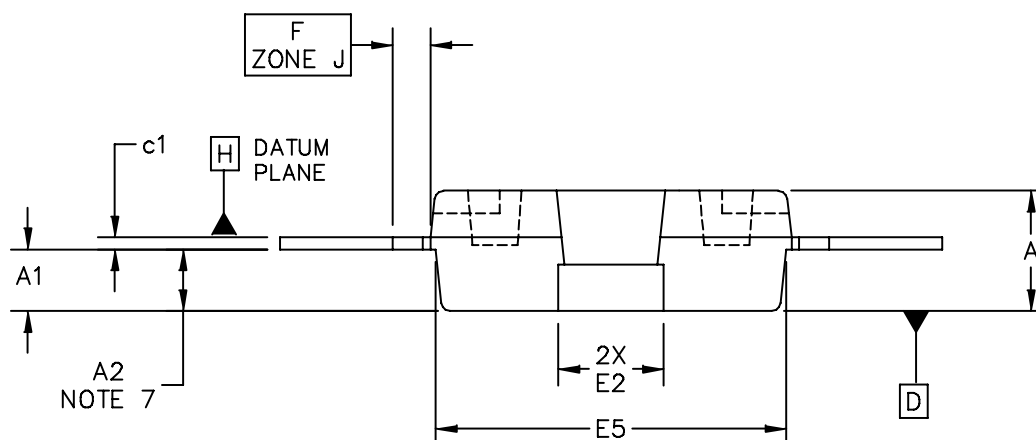
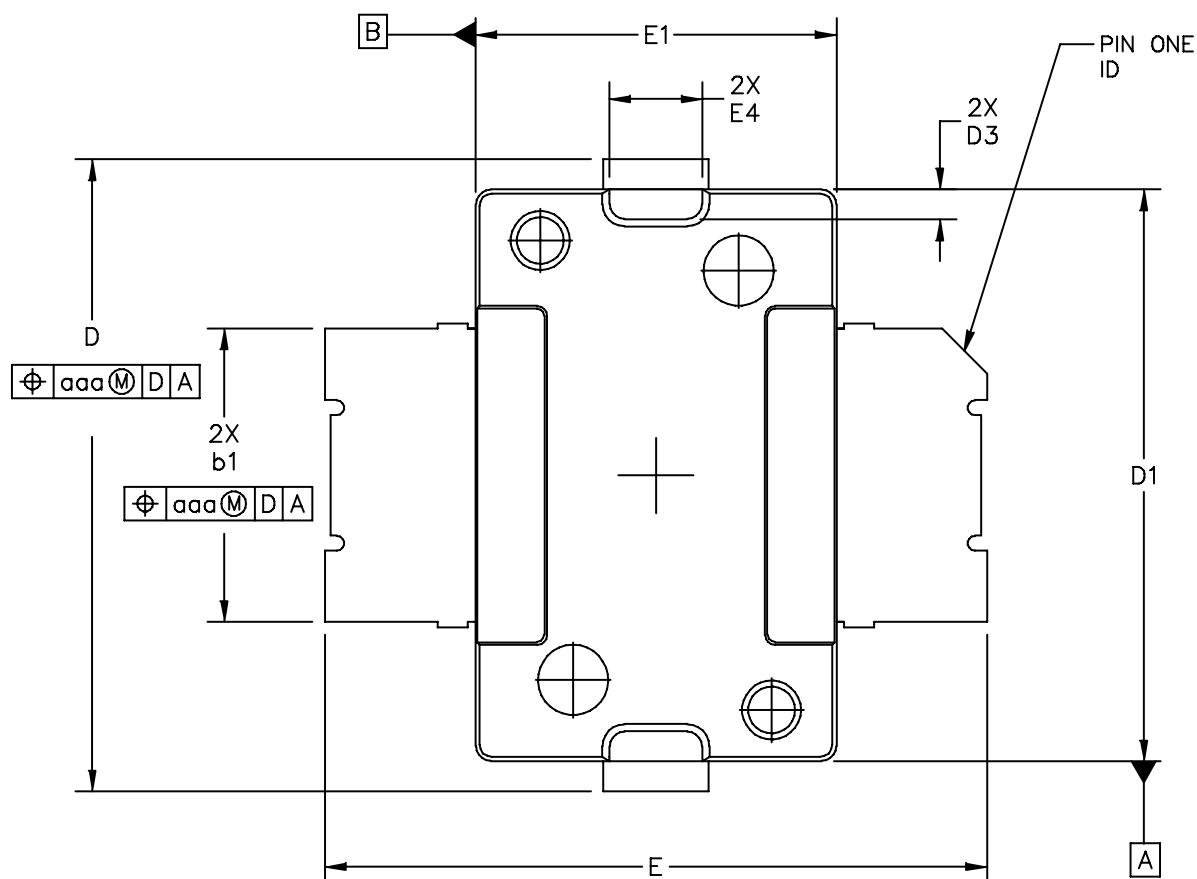


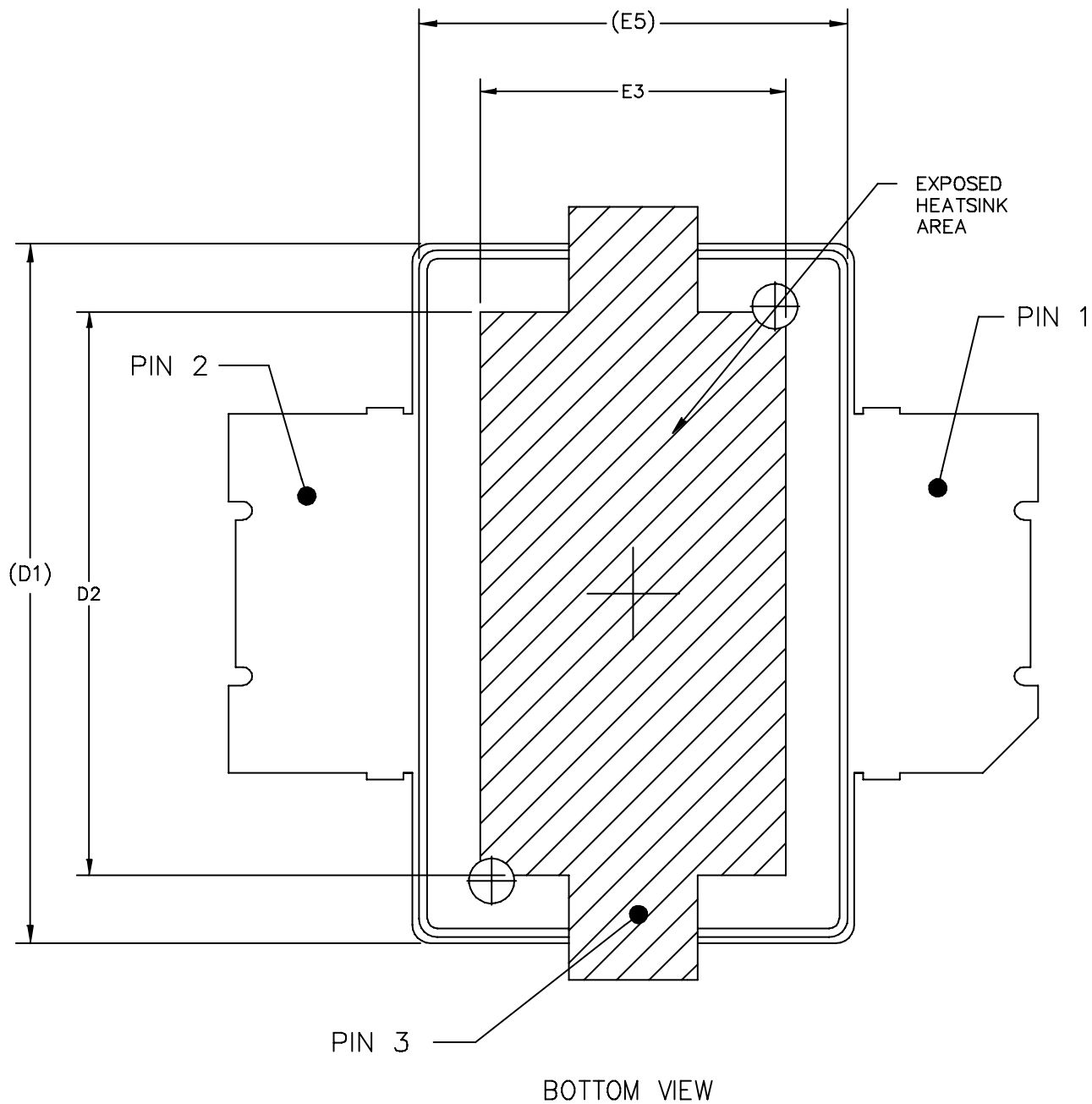
Figure 16. Series Equivalent Source and Load Impedance

PACKAGE DIMENSIONS



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TITLE: TO-270 SURFACE MOUNT		DOCUMENT NO: 98ASH98117A	REV: K
		CASE NUMBER: 1265-09	29 JUN 2007
		STANDARD: JEDEC TO-270 AA	

MRF6S9045NR1 MRF6S9045NBR1



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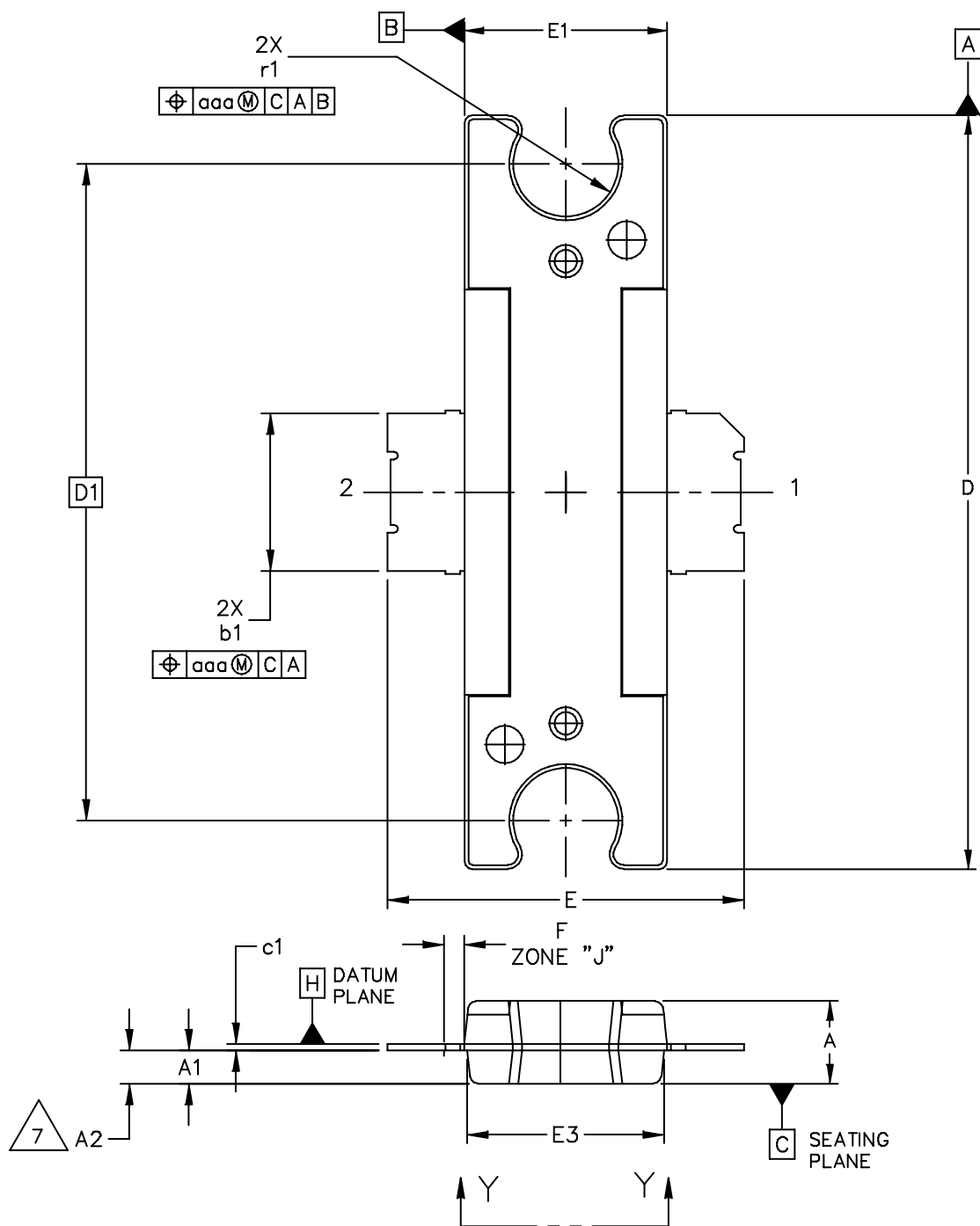
NOTES:

1. CONTROLLING DIMENSION: INCH
2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
3. DATUM PLANE -H- IS LOCATED AT TOP OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE TOP OF THE PARTING LINE.
4. DIMENSIONS "D1" AND "E1" DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS .006 PER SIDE. DIMENSIONS "D1 AND "E1" DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE -H-.
5. DIMENSION "b1" DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .005 TOTAL IN EXCESS OF THE "b1" DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. DATUMS -A- AND -B- TO BE DETERMINED AT DATUM PLANE -H-.
7. DIMENSION "A2" APPLIES WITHIN ZONE "J" ONLY.
8. DIMENSIONS "D" AND "E2" DO NOT INCLUDE MOLD PROTRUSION. OVERALL LENGTH INCLUDING MOLD PROTRUSION SHOULD NOT EXCEED 0.430 INCH FOR DIMENSION "D" AND 0.080 INCH FOR DIMENSION "E2". DIMENSIONS "D" AND "E2" DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE -D-.

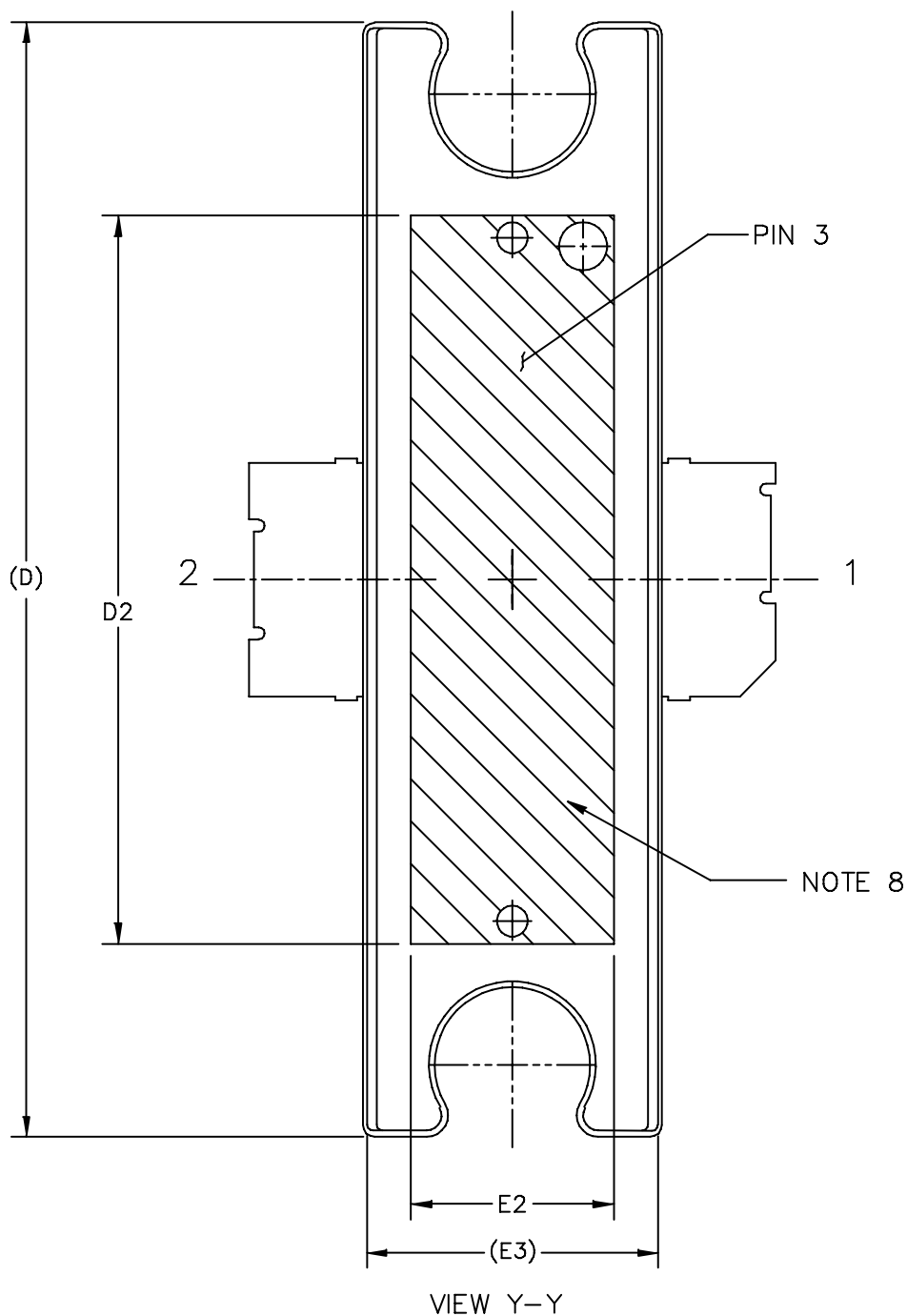
STYLE 1:

PIN 1 - DRAIN
PIN 2 - GATE
PIN 3 - SOURCE

INCH		MILLIMETER		INCH		MILLIMETER	
DIM	MIN	MAX	MIN	MAX	DIM	MIN	MAX
A	.078	.082	1.98	2.08	F	.025 BSC	0.64 BSC
A1	.039	.043	0.99	1.09	b1	.193 .199	4.90 5.06
A2	.040	.042	1.02	1.07	c1	.007 .011	0.18 0.28
D	.416	.424	10.57	10.77	aaa	.004	0.10
D1	.378	.382	9.60	9.70			
D2	.290	----	7.37	----			
D3	.016	.024	0.41	0.61			
E	.436	.444	11.07	11.28			
E1	.238	.242	6.04	6.15			
E2	.066	.074	1.68	1.88			
E3	.150	----	3.81	----			
E4	.058	.066	1.47	1.68			
E5	.231	.235	5.87	5.97			
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					CASE NUMBER: 1265-09		29 JUN 2007
					STANDARD: JEDEC TO-270 AA		



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		CASE NUMBER: 1337-04	10 SEP 2007
		STANDARD: JEDEC TO-272 BC	



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TITLE: TO-272 2 LEAD	DOCUMENT NO: 98ASA99191D		REV: E
	CASE NUMBER: 1337-04		10 SEP 2007
	STANDARD: JEDEC TO-272 BC		

NOTES:

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3. DATUM PLANE -H- IS LOCATED AT THE TOP OF LEAD AND IS COINCIDENT WITH THE LEAD WHERE THE LEAD EXITS THE PLASTIC BODY AT THE TOP OF THE PARTING LINE.
4. DIMENSIONS "D" AND "E1" DO NOT INCLUDE MOLD PROTRUSION. ALLOWABLE PROTRUSION IS .006 PER SIDE. DIMENSIONS "D" AND "E1" DO INCLUDE MOLD MISMATCH AND ARE DETERMINED AT DATUM PLANE -H-.
5. DIMENSIONS "b1" DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE .005 TOTAL IN EXCESS OF THE "b1" DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. DATUMS -A- AND -B- TO BE DETERMINED AT DATUM PLANE -H-.
7. DIMENSION A2 APPLIES WITHIN ZONE "J" ONLY.
8. HATCHING REPRESENTS THE EXPOSED AREA OF THE HEAT SLUG.

STYLE 1:
 PIN 1 - DRAIN
 PIN 2 - GATE
 PIN 3 - SOURCE

INCH			MILLIMETER		INCH			MILLIMETER	
DIM	MIN	MAX	MIN	MAX	DIM	MIN	MAX	MIN	MAX
A	.100	.104	2.54	2.64	b1	.193	.199	4.90	5.05
A1	.039	.043	0.99	1.09	c1	.007	.011	0.18	0.28
A2	.040	.042	1.02	1.07	r1	.063	.068	1.60	1.73
D	.928	.932	23.57	23.67	aaa	.004		0.1	
D1	.810 BSC		20.57 BSC						
D2	.604	----	15.34	----					
E	.438	.442	11.12	11.23					
E1	.248	.252	6.30	6.40					
E2	.162	----	4.11	----					
E3	.241	.245	6.12	6.22					
F	.025 BSC		0.64 BSC						
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TITLE: TO-272 2 LEAD					DOCUMENT NO: 98ASA99191D			REV: E	
					CASE NUMBER: 1337-04			10 SEP 2007	
					STANDARD: JEDEC TO-272 BS				

PRODUCT DOCUMENTATION

Refer to the following documents to aid your design process.

Application Notes

- AN1907: Solder Reflow Attach Method for High Power RF Devices in Plastic Packages
- AN1955: Thermal Measurement Methodology of RF Power Amplifiers
- AN3263: Bolt Down Mounting Method for High Power RF Transistors and RFICs in Over-Molded Plastic Packages

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
4	Aug. 2008	• Listed replacement part and Device Migration notification reference number, p. 1 • Listed MRF6S9045NBR1 as no longer manufactured, p. 1 • Replaced Case Outline 1265-08 with 1265-09, Issue K, p. 1, 11-13. Corrected cross hatch pattern in bottom view and changed its dimensions (D2 and E3) to minimum value on source contact (D2 changed from Min-Max .290-.320 to .290 Min; E3 changed from Min-Max .150-.180 to .150 Min). Added JEDEC Standard Package Number. • Replaced Case Outline 1337-03 with 1337-04, p. 1, 14-16. Issue D: Removed Drain-ID label from View Y-Y on Sheet 2. Renamed E2 to E3. Added cross-hatch region dimensions D2 and E2. Added JEDEC Standard Package Number. Issue E: Corrected document number 98ASA99191D on Sheet 3. • Removed Total Device Dissipation from Max Ratings table as data was redundant (information already provided in Thermal Characteristics table), p. 1 • Added Case Operating Temperature limit to the Maximum Ratings table and set limit to 150°C, p. 1 • Operating Junction Temperature increased from 200°C to 225°C in Maximum Ratings table, related "Continuous use at maximum temperature will affect MTTF" footnote added and changed 200°C to 225°C in Capable Plastic Package bullet, p. 1 • Corrected V_{DS} to V_{DD} in the RF test condition voltage callout for $V_{GS(Q)}$ and added "Measured in Functional Test", On Characteristics table, p. 2 • Removed Forward Transconductance from On Characteristics table as it no longer provided usable information, p. 2 • Corrected C_{iss} test condition to indicate AC stimulus on the V_{GS} connection versus the V_{DS} connection, Dynamic Characteristics table, p. 2 • Updated Part Numbers in Table 6 Component Designations and Values, to latest RoHS compliant part numbers, p. 4 • Adjusted scale for Fig. 5, Two-Tone Power Gain versus Output Power, to better match the device's capabilities, p. 6 • Removed lower voltage tests from Fig. 12, Power Gain versus Output Power, due to fixed tuned fixture limitations, p. 8 • Replaced Fig. 13, MTTF versus Junction Temperature with updated graph. Removed Amps² and listed operating characteristics and location of MTTF calculator for device, p. 8 • Added Product Documentation and Revision History, p. 17

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